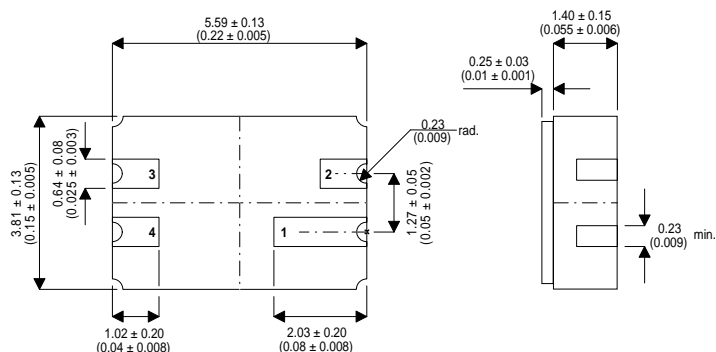


## MECHANICAL DATA

Dimensions in mm (inches)



**(LCC3 PACKAGE)**  
**Underside View**

PAD 1 — Cathode                      PAD 3 — No Connection  
PAD 2 — No Connection              PAD 4 — Anode

## GENERAL PURPOSE SILICON RECTIFIER DIODE

General Purpose Rectifier Diode  
In Hermetic Ceramic Surface Mount Package  
For High Reliability Applications

## ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_R$	Reverse Voltage			200	V
$V_{RRM}$	Peak Reverse Voltage			200	V
$I_{F(AV)}$	Average Half Wave Rectified Forward Current			$T_{amb} \leq 25^{\circ}\text{C}$	1.0
				$T_{amb} = 100^{\circ}\text{C}$	0.75
$I_F$	D.C Forward Current			1	A
$I_{FRM}$	Repetitive Peak Forward Current			10	A
$I_{FSM}$	Non-Repetitive Peak Forward Current	(half cycle surge , 60 c.p.s)		30	A

$T_{stg}$	Storage Temperature Range	-55 to +175 °C
$T_j$	Max junction temperature	+150°C

## CHARACTERISTICS ( $T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$	Forward Voltage Drop			1.1	V
$V_{F(AV)}$	Full-Cycle average forward voltage drop			0.8	V
$I_R$	Reverse Current			$V_R = 50\text{ V} , T_{amb} = 25^{\circ}\text{C}$	10
				$V_R = 50\text{ V} , T_{amb} = 100^{\circ}\text{C}$	50
$I_{R(AV)}$	Full cycle average reverse current			30	$\mu\text{A}$